

FIG. 1A

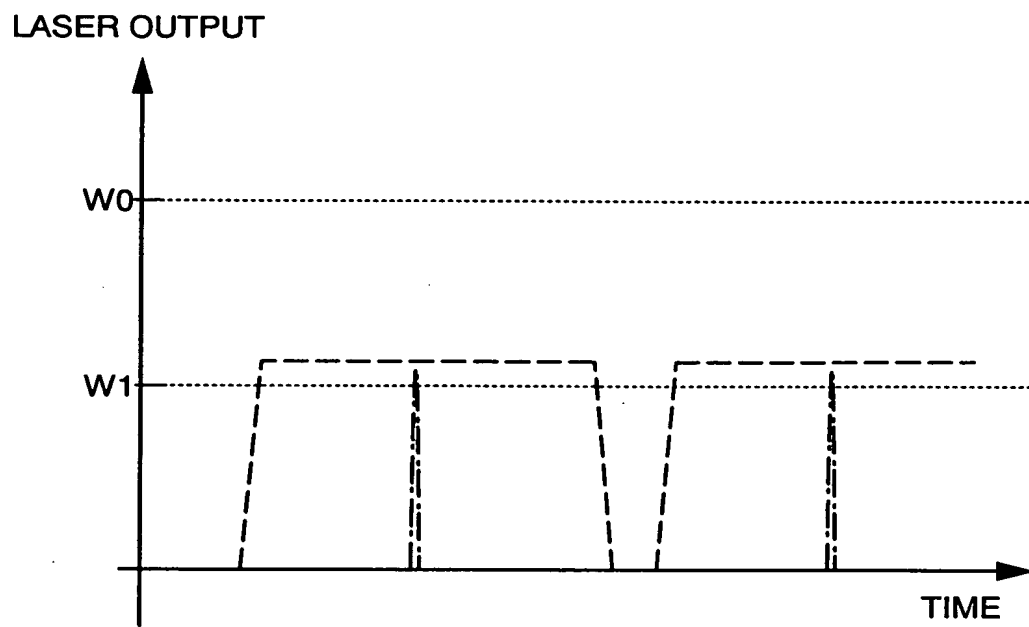
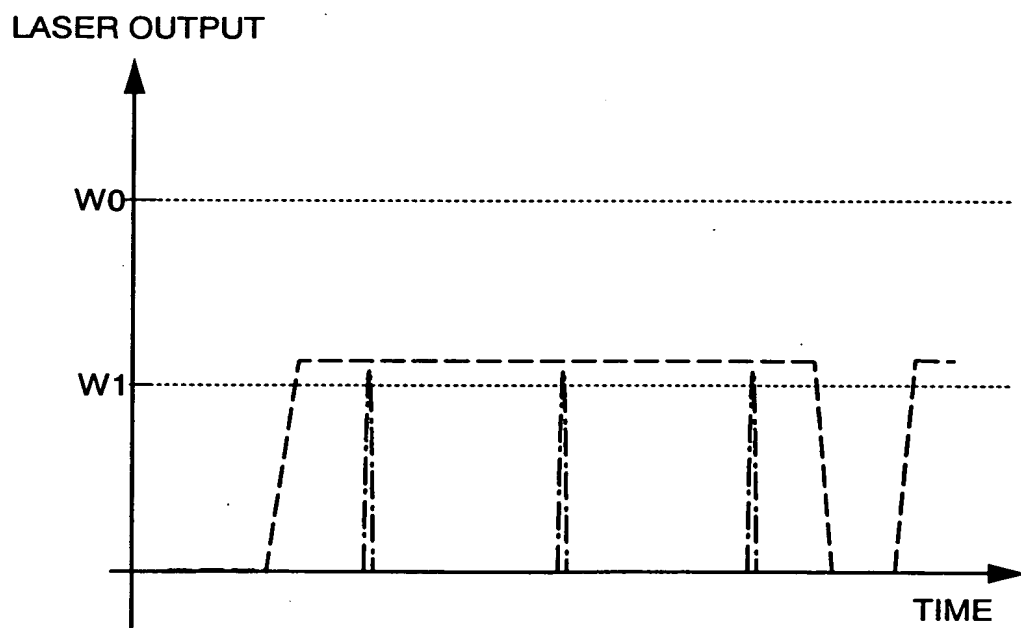


FIG. 1B



----- 1ST PULSE LASRE

----- 2ND PULSE LASER

FIG. 2

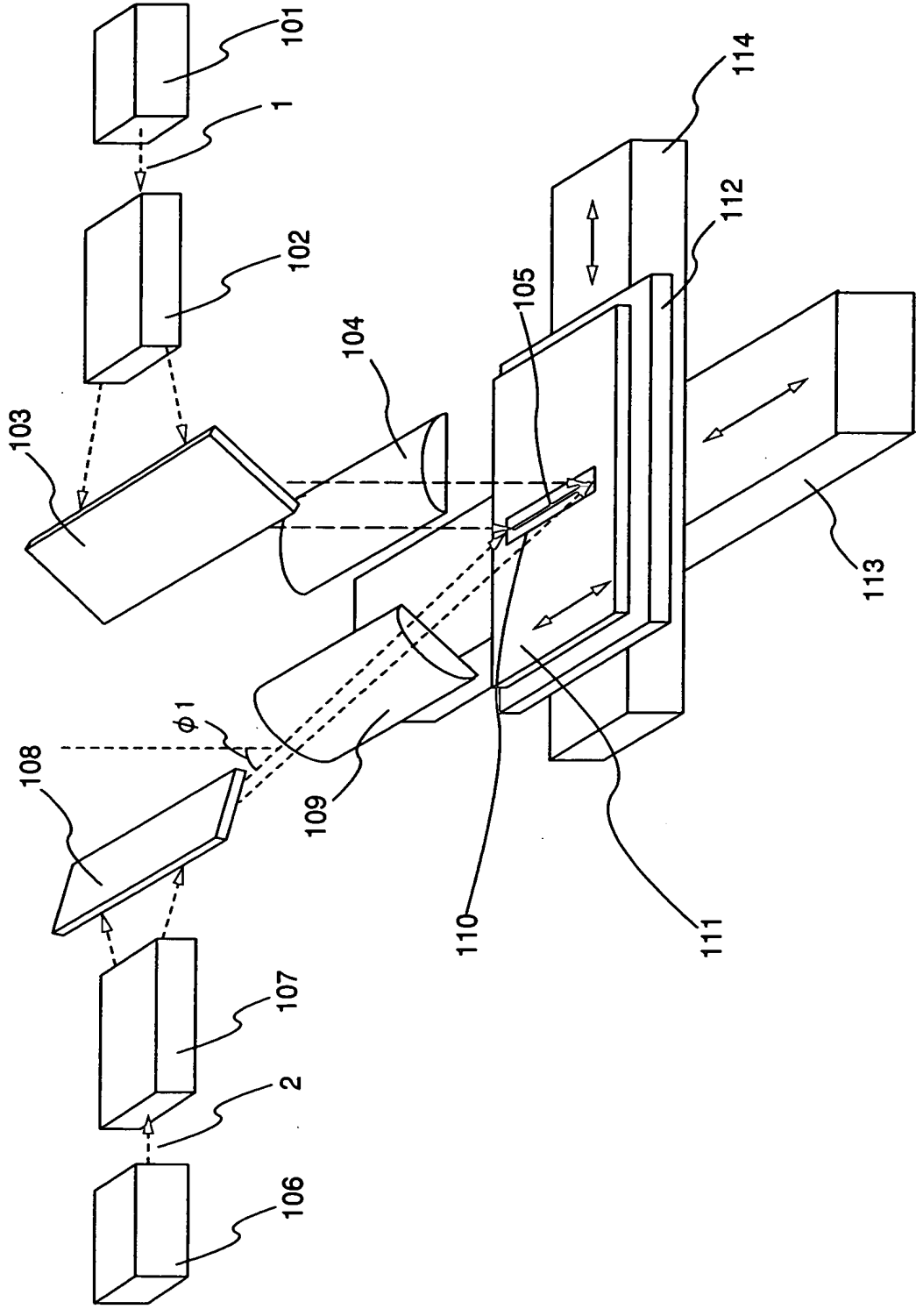


FIG. 3A

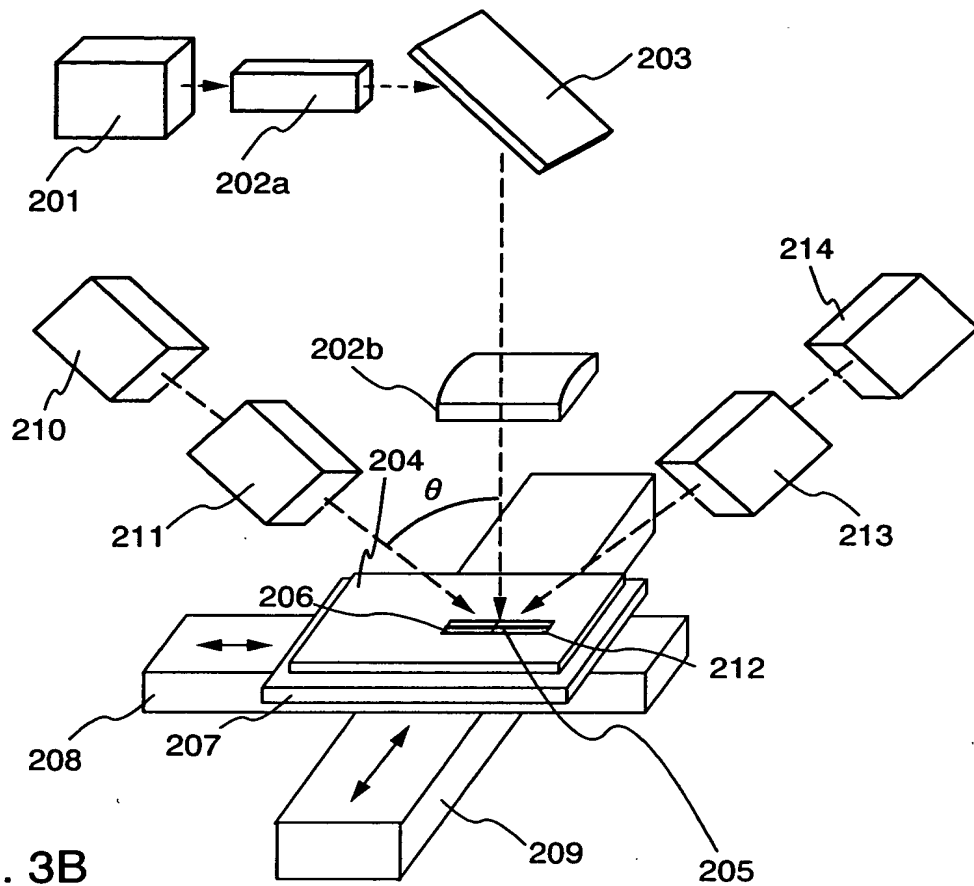


FIG. 3B

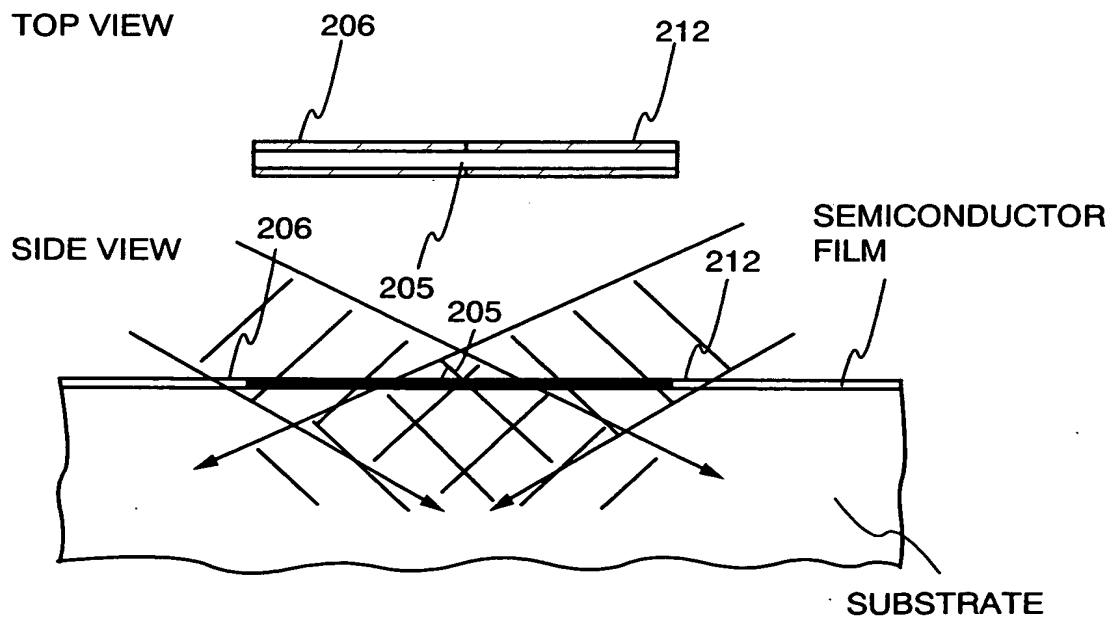


FIG. 4

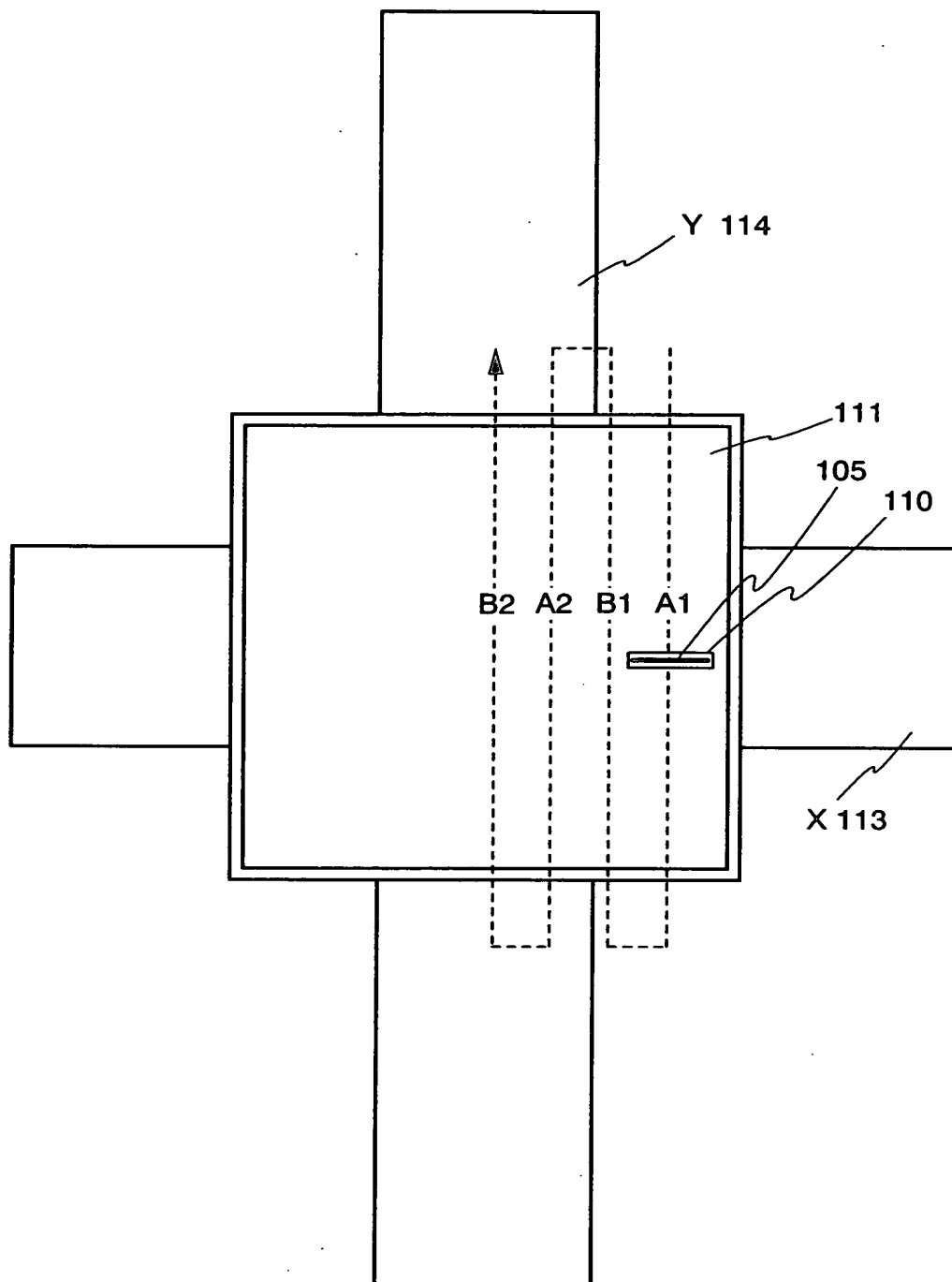


FIG. 5A

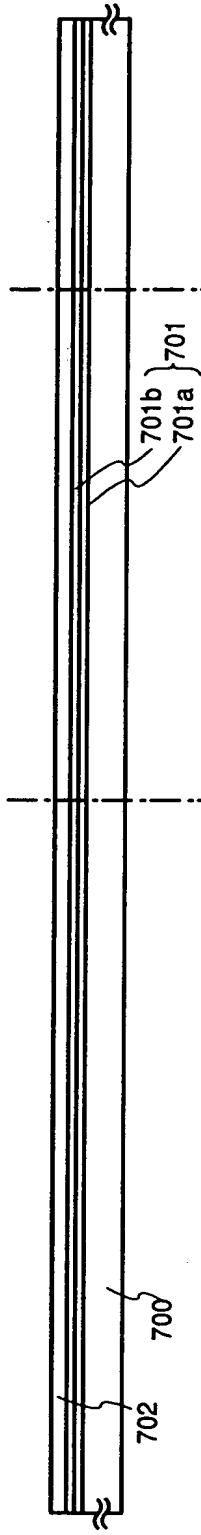


FIG. 5B

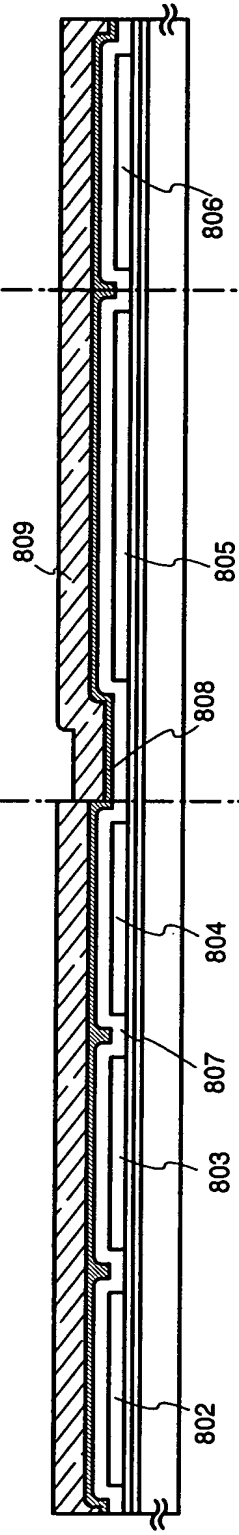


FIG. 5C

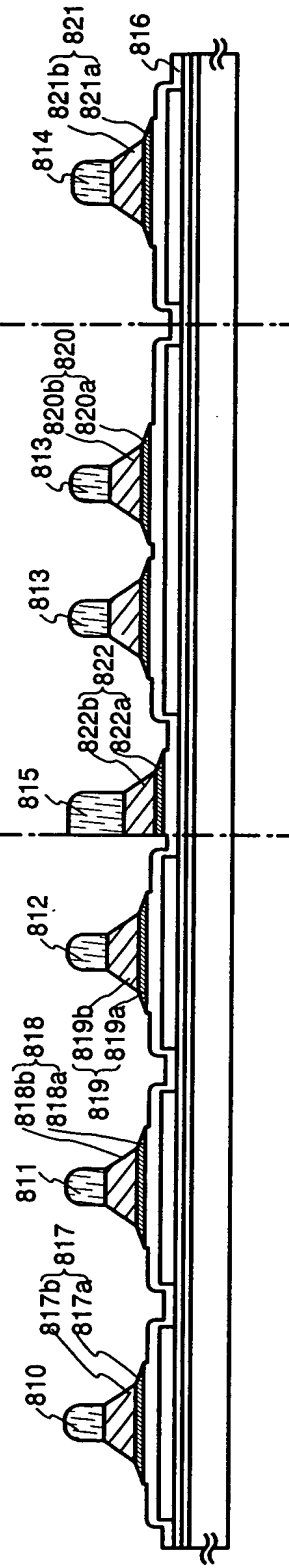


FIG. 6A

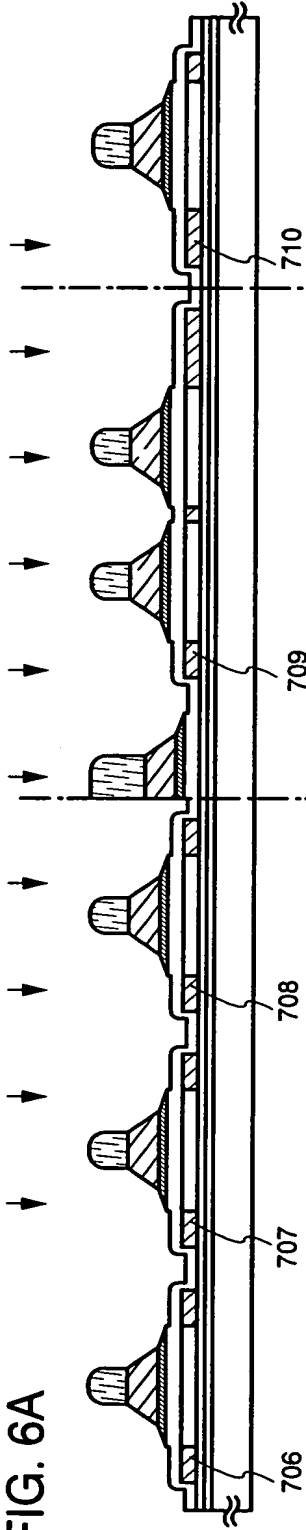


FIG. 6B

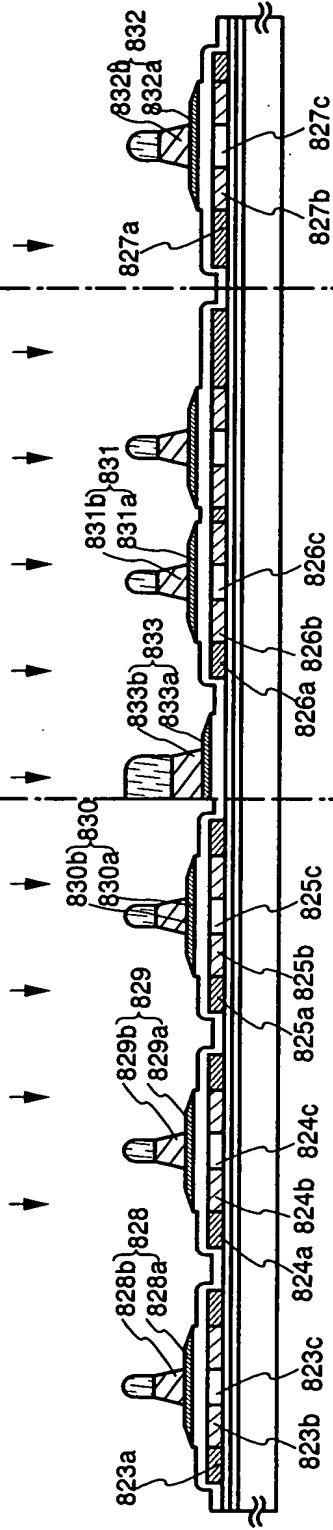


FIG. 6C

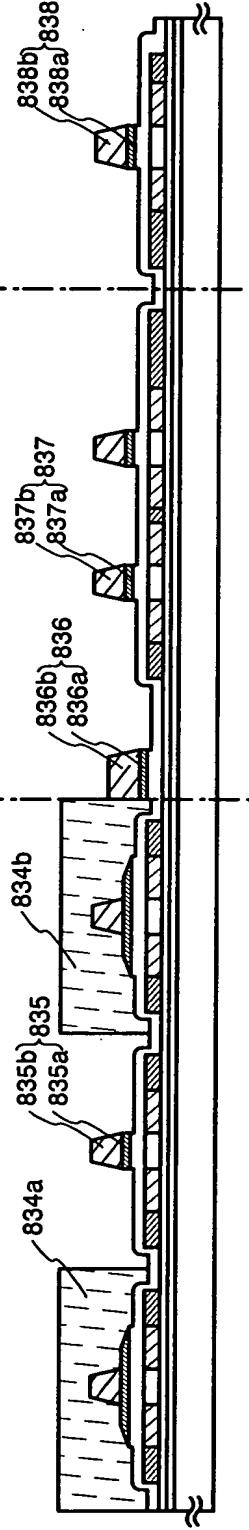


FIG. 7A

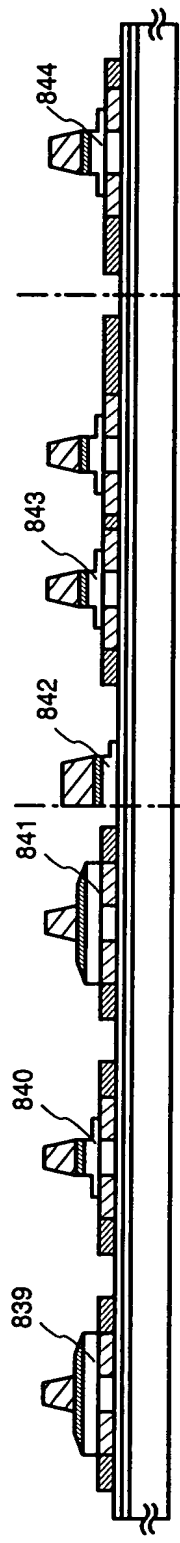


FIG. 7B

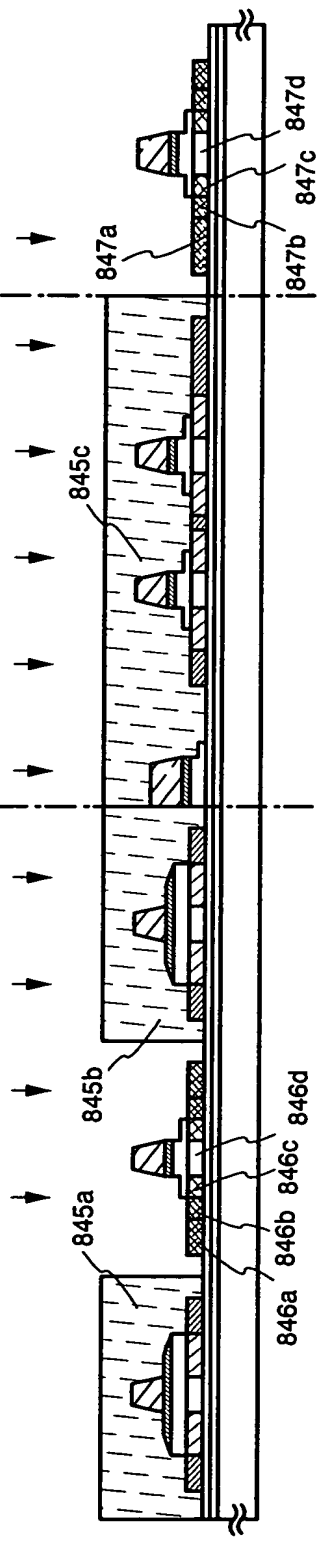


FIG. 7C

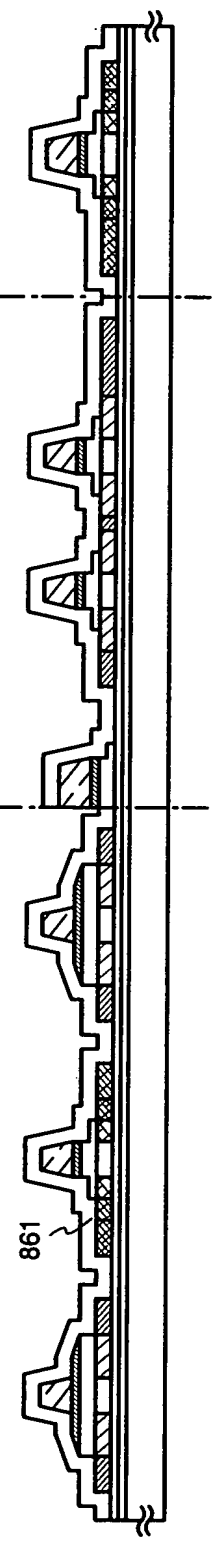


Fig. 8 is a cross-sectional view of a semiconductor device. The device is divided into two main sections: a CMOS circuit (906) on the left and a second circuit (907) on the right. The CMOS circuit (906) contains three transistors (901, 902, 903). The second circuit (907) contains two transistors (904, 905). The device includes various layers and structures labeled 862 through 870. A dashed line indicates a cross-section through the device.

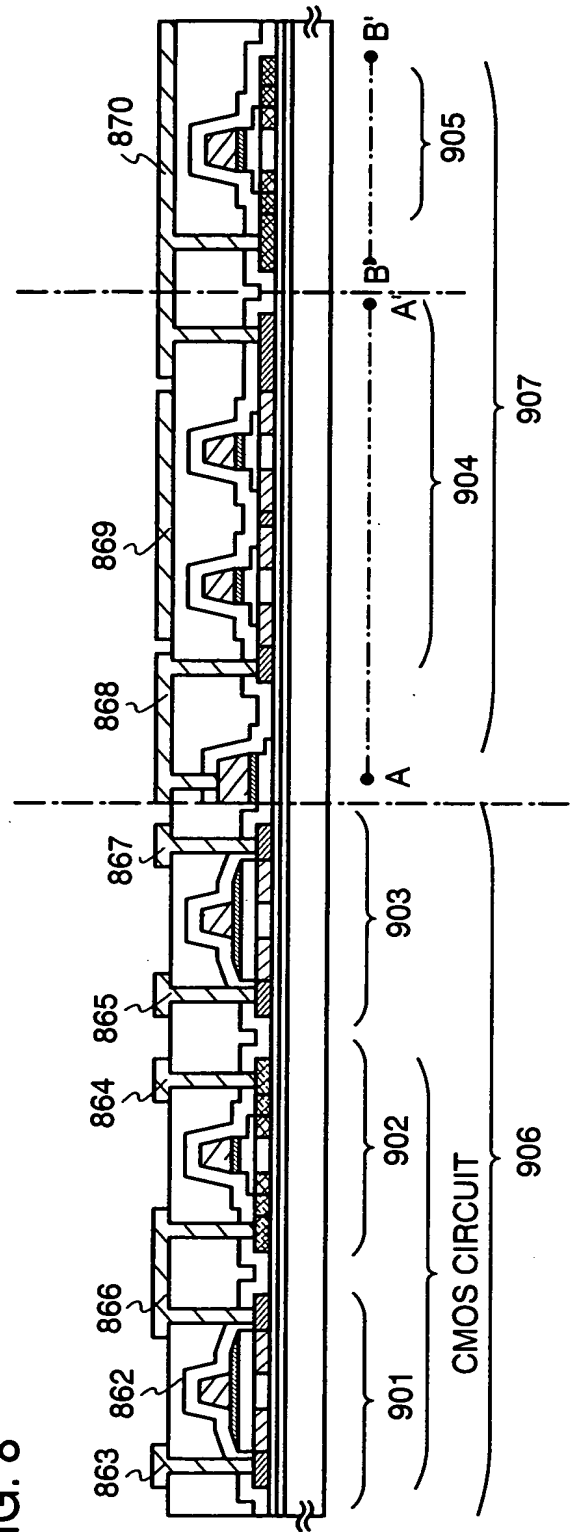




FIG. 9

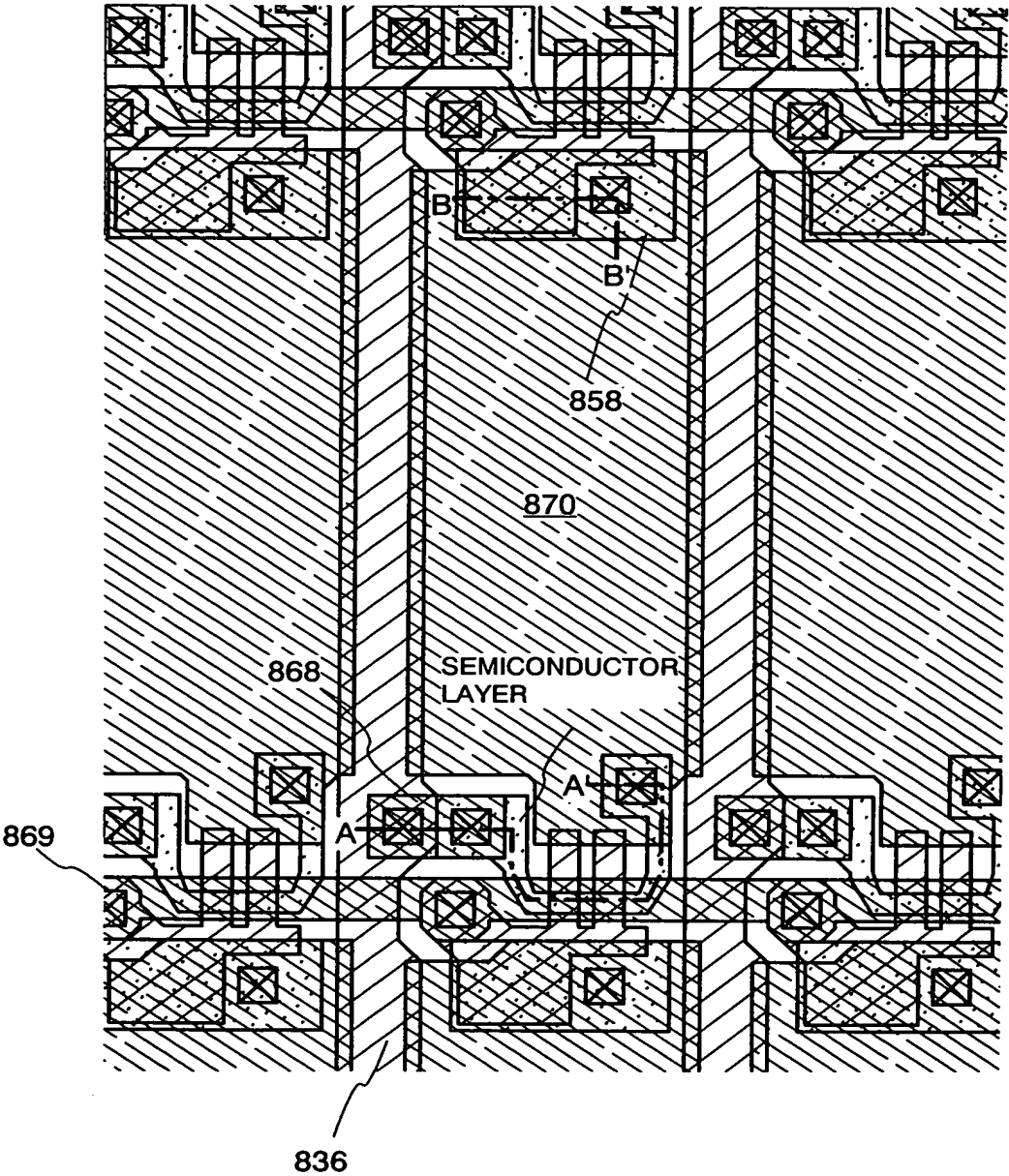


FIG. 10

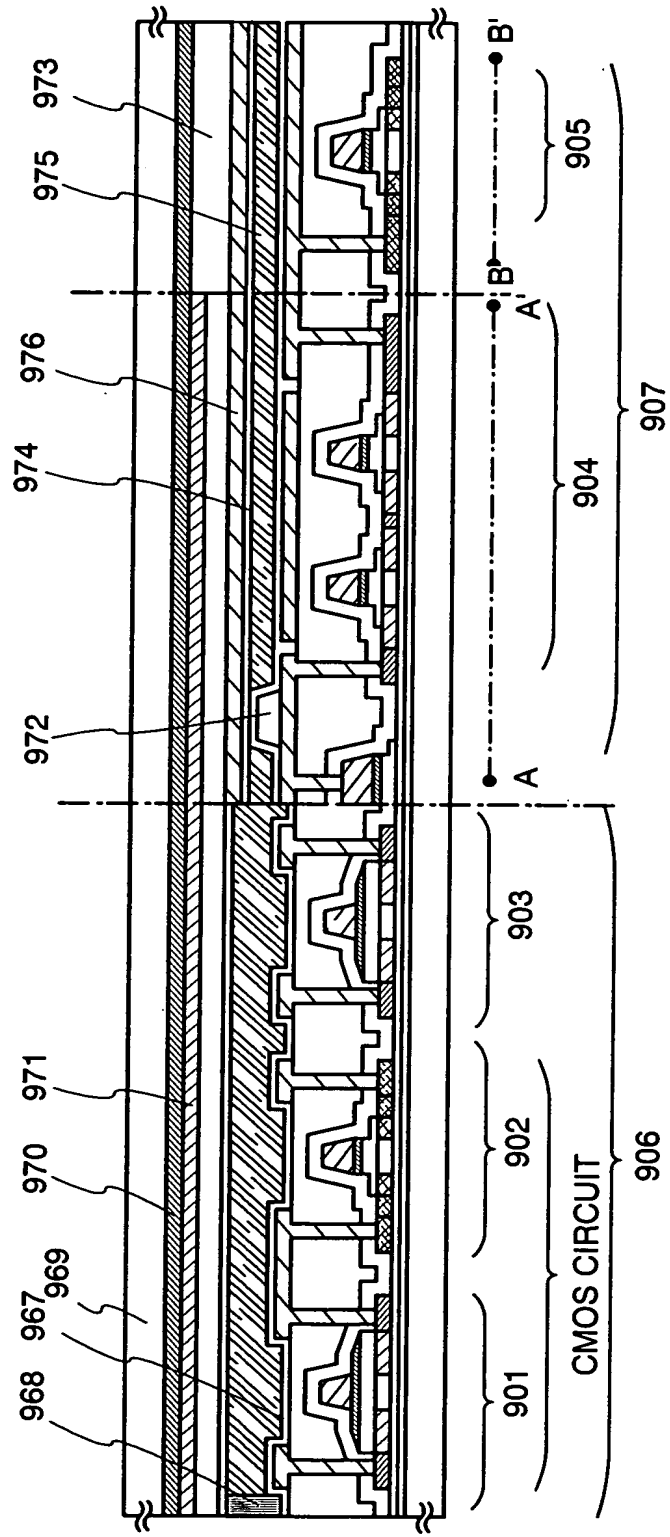
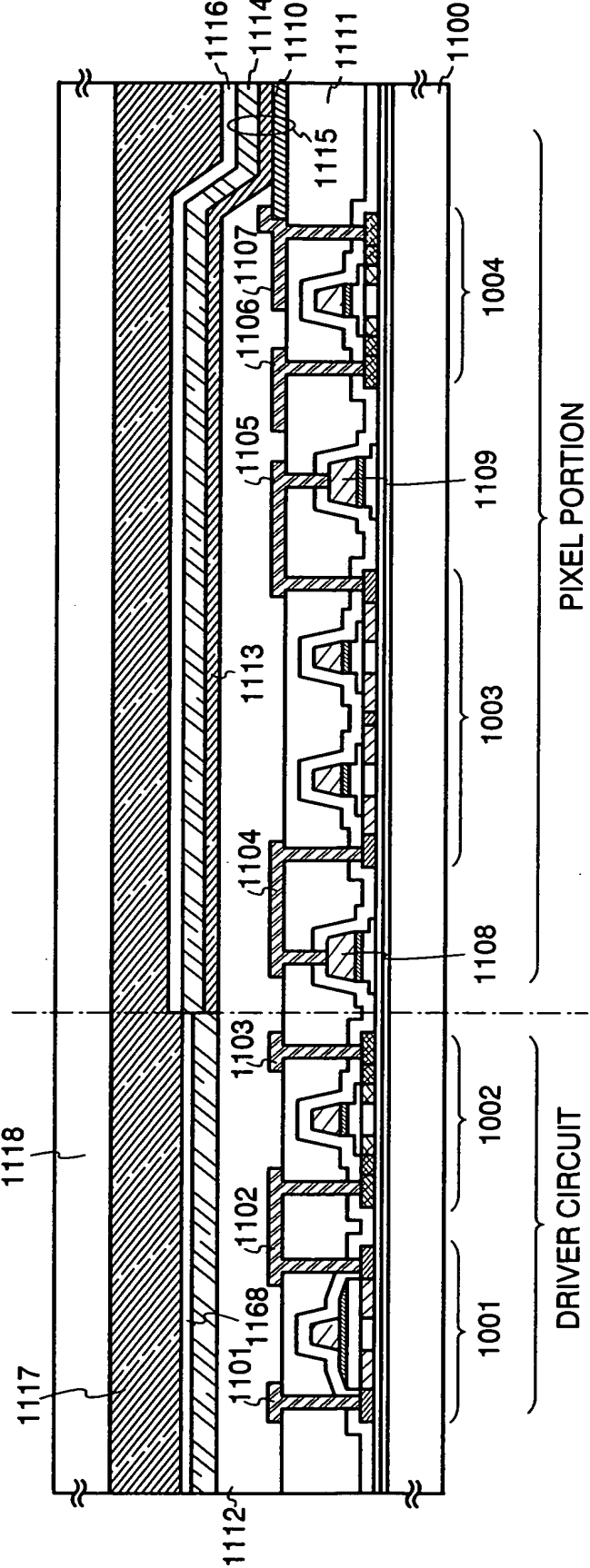


FIG. 11



This cross-sectional view shows the internal structure of the device. The substrate 1303 is at the base. A layer 1305 is on the left. A central layer 1301 contains a series of stacked layers: 1001, 1002, 1004, 1110, 1112, 1114, and 1116. A layer 1302 is on the right. A layer 1304 is at the bottom. A layer 1307 is on the left. A layer 1207 is on the right. A layer 1206 is at the bottom. An arrow labeled "LIGHT EMITTING DIRECTION" points to the right. The cross-section is labeled A-A'.

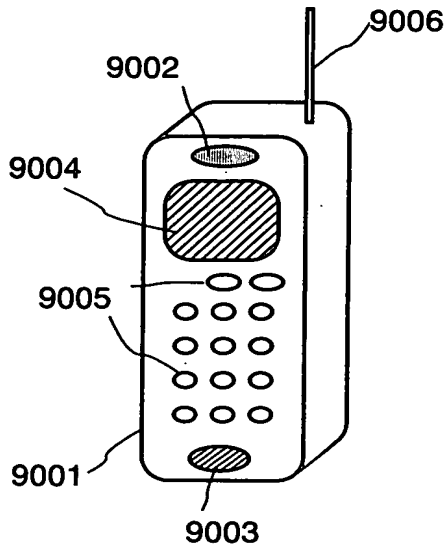


FIG. 13A

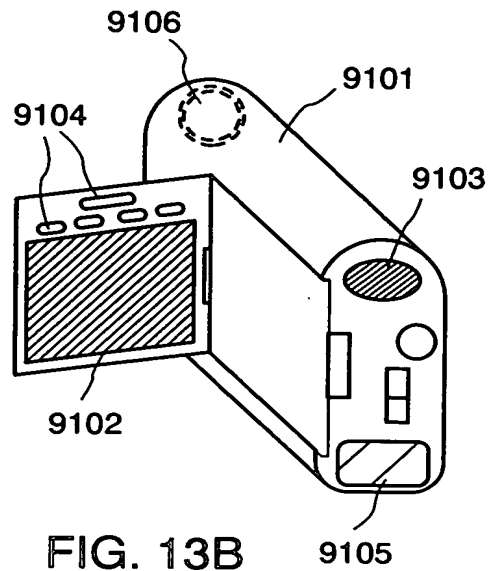


FIG. 13B

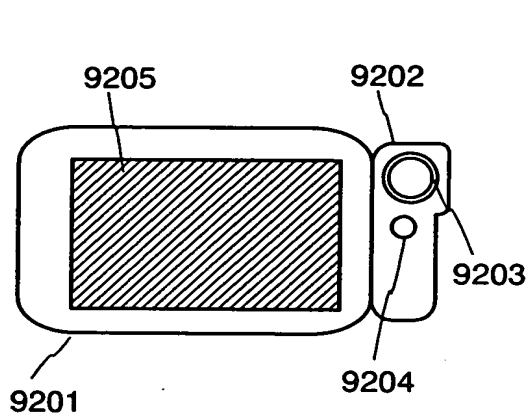


FIG. 13C

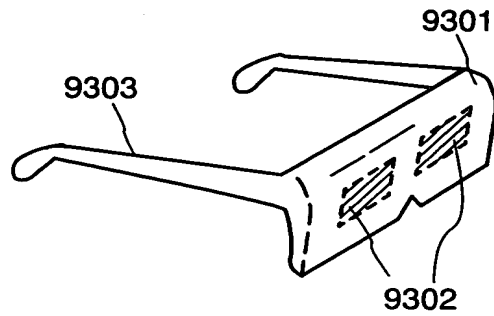


FIG. 13D

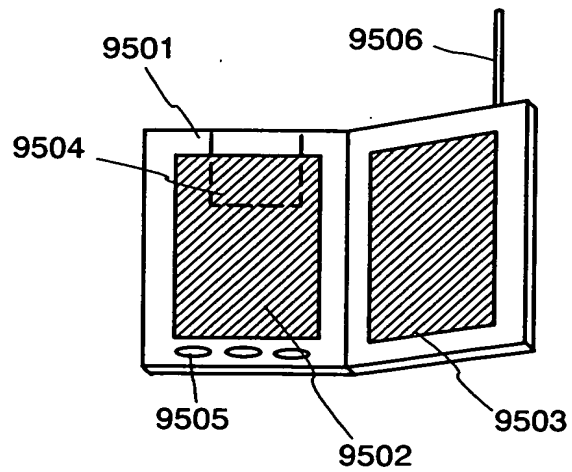


FIG. 13E

FIG. 14A

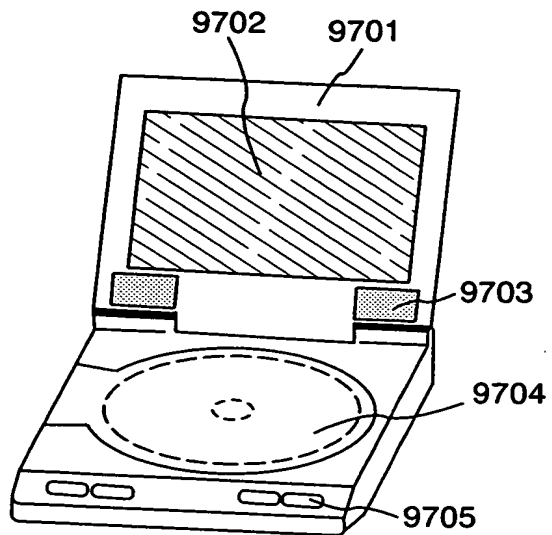


FIG. 14B

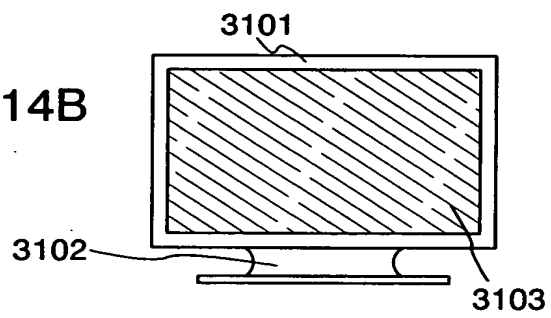
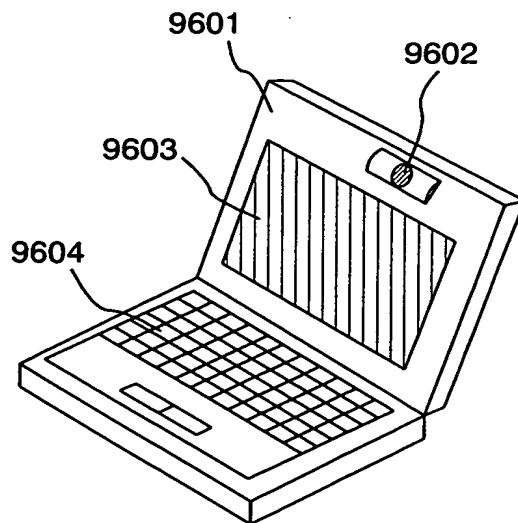


FIG. 14C



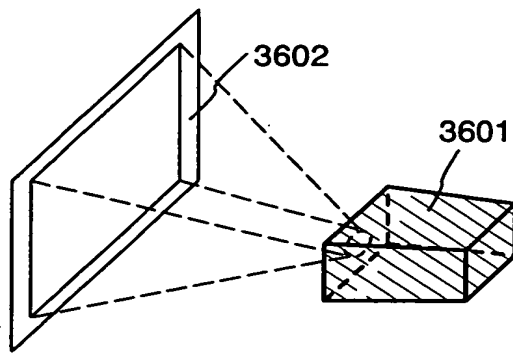


FIG. 15A

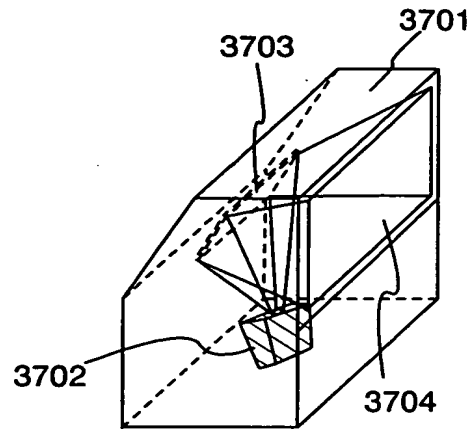


FIG. 15B

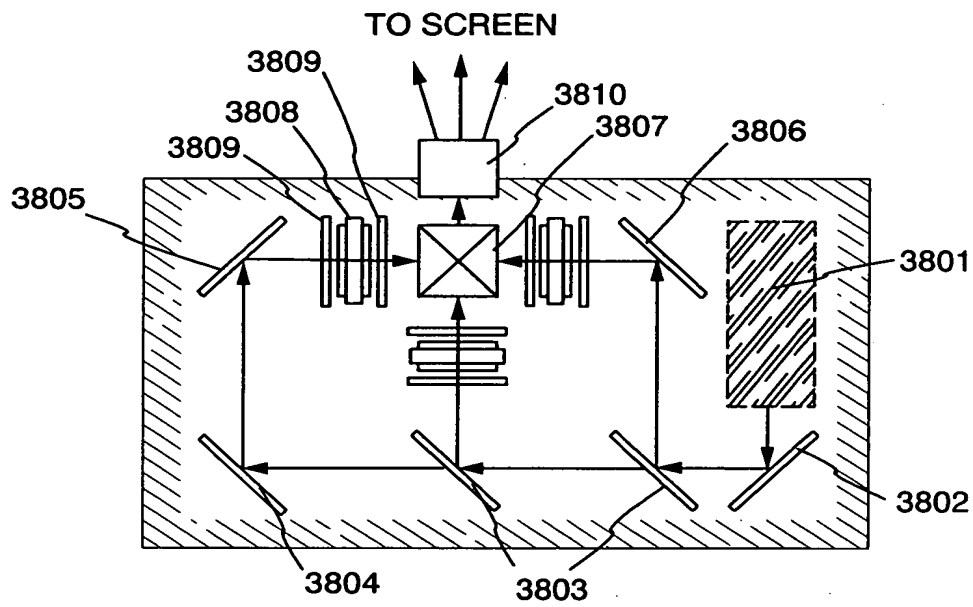


FIG. 15C

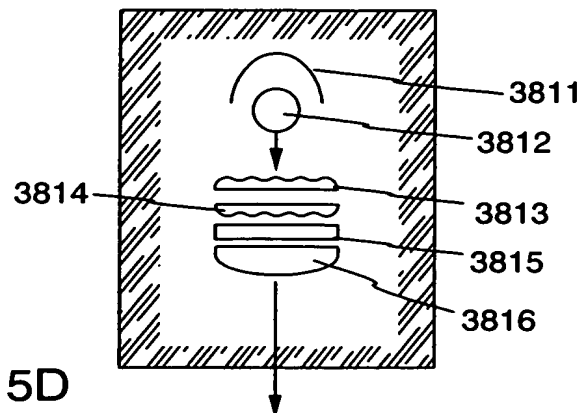


FIG. 15D